NSN 5962-01-420-6416

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Bodv	l er	nath:
Douv	LCI	ıuıı.

Between 0.342 inches and 0.358 inches

Body Width:

Between 0.342 inches and 0.358 inches

Body Height:

Between 0.060 inches and 0.078 inches

Maximum Power Dissipation Rating:

1.0 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Pacer dawn

Features Provided:

Burn in, mil-std-883, class b and electrostatic sensitive and monolithic and programmed and tested to mil-std-883

Inclosure Material:

Ceramic

Inclosure Configuration:

Leadless flat pack

Output Logic Form:

Complementary-metal oxide-semiconductor logic

Input Circuit Pattern:

16 input

Criticality Code Justification:

Cbbl

Case Outline Source And Designator:

C-2a mil-m-38510

Current Rating Per Characteristic:

24.00 milliamperes reverse current, dc

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit, programmed (pal c16l8-20)

Voltage Rating And Type Per Characteristic:

-0.5 volts power source and 7.0 volts power source and -3.0 volts input and 7.0 volts input

Capitance Rating Per Characteristic:

7.00 input picofarads and 7.00 output picofarads

Time Rating Per Chacteristic:

20.00 nanoseconds af output megawatts

Memory Device Type:

Pal

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Special Features

Altered item programmed using 67268 5962-8871309xa

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

20 leadless

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

Fiig:

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